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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number & Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
RE		EP 0143700 A2	6/1985	BAUDRANT et al.			
PH		EP 0077200 A2	4/1980	KATO et al.			
PF		WO 02/09167 A3	1/2002	PARSONS			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
FO		CHAMBERS and PARSONS, "Yttrium silicate formation on silicon: Effect of silicon preoxidation and nitridation on interface reaction kinetics" Applied Physics Letters 77(15), 9 October 2000, pp. 2385-2387	
PR		GURVITCH et al., "Study of thermally oxidized yttrium films on silicon" Applied Physics Letter 51(12), 21 September 1987, pp. 919-921	
RO		KALKUR et al., "Yttrium oxide based metal-insulator-semiconductor structures on silicon" Thin Solid Films 170, 1989, pp. 185-189.	
RE		PIERSON, HUGH, O., Handbook of Chemical Vapor Deposition, Noyes Publications, Park Ridge, New Jersey pp. 229-230.	

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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